Dual 4-Stage Binary Ripple Counter with ÷ 2 and ÷ 5 Sections

High-Performance Silicon-Gate CMOS

The MC74HC390A is identical in pinout to the LS390. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two independent 4-bit counters, each composed of a divide-by-two and a divide-by-five section. The divide-by-two and divide-by-five counters have separate clock inputs, and can be cascaded to implement various combinations of \div 2 and/or \div 5 up to a \div 100 counter.

Flip—flops internal to the counters are triggered by high—to—low transitions of the clock input. A separate, asynchronous reset is provided for each 4—bit counter. State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used as clocks or strobes except when gated with the Clock of the HC390A.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No 7A
- Chip Complexity: 244 FETs or 61 Equivalent Gates

CLOCK A 1, 15 ÷ 2 3, 13 QA CLOCK B 4, 12 ÷ 5 COUNTER 7, 9 QC QD

NOTION TABLE

ı	TONCTION TABLE								
	Clock		To a to the second						
	Α	В	Reset	Action					
	Х	Х	Н	Reset ÷ 2 and ÷ 5					
	~	Χ	L	Increment ÷ 2					
	Х	_	L	Increment ÷ 5					



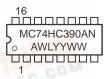
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MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SO-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



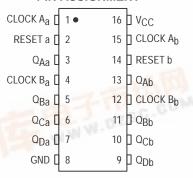
A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping
MC74HC390AN	PDIP-16	2000 / Box
MC74HC390AD	SOIC-16	48 / Rail
MC74HC390ADR2	SOIC-16	2500 / Reel
MC74HC390ADT	TSSOP-16	96 / Rail
MC74HC390ADTR2	TSSOP-16	2500 / Reel



PIN $16 = V_{CC}$ PIN 8 = GND

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V_{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			VCC	V
TA	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time	3.0 V 4.5 V	0 0 0	1000 600 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
VIL	Maximum Low–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	٧
Voн	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	٧
		V_{in} = V_{IH} or V_{IL} $ I_{out} \le 2.4$ mA $ I_{out} \le 4.0$ mA $ I_{out} \le 5.2$ mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	>
		V_{in} = V_{IH} or V_{IL} $ I_{out} \le 2.4$ mA $ I_{out} \le 4.0$ mA $ I_{out} \le 5.2$ mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	

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^{*}Maximum Ratings are those values beyond which damage to the device may occur.

[†]Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
lin	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μА
lcc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Guaranteed Limit			
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
fmax	Maximum Clock Frequency (50% Duty Cycle)	2.0	10	9	8	MHz
	(Figures 1 and 3)	3.0	15	14	12	
		4.5	30	28	25	
		6.0	50	45	40	
tpLH,	Maximum Propagation Delay, Clock A to QA	2.0	70	80	90	ns
^t PHL	(Figures 1 and 3)	3.0	40	45	50	
		4.5	24	30	36	
		6.0	20	26	31	
tPLH,	Maximum Propagation Delay, Clock A to QC	2.0	200	250	300	ns
^t PHL	(QA connected to Clock B)	3.0	160	185	210	
	(Figures 1 and 3)	4.5	58	65	70	
		6.0	49	62	68	
t _{PLH} ,	Maximum Propagation Delay, Clock B to QB	2.0	70	80	90	ns
t _{PHL}	(Figures 1 and 3)	3.0	40	45	50	
		4.5	26	33	39	
		6.0	22	28	33	
tPLH,	Maximum Propagation Delay, Clock B to QC	2.0	90	105	180	ns
^t PHL	(Figures 1 and 3)	3.0	56	70	100	
		4.5	37	46	56	
		6.0	31	39	48	
tPLH,	Maximum Propagation Delay, Clock B to QD	2.0	70	80	90	ns
^t PHL	(Figures 1 and 3)	3.0	40	45	50	
		4.5	26	33	39	
		6.0	22	28	33	
^t PHL	Maximum Propagation Delay, Reset to any Q	2.0	80	95	110	ns
	(Figures 2 and 3)	3.0	48	65	75	
		4.5	30	38	44	
		6.0	26	33	39	
tTLH,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
tTHL	(Figures 1 and 3)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	15	19	
C _{in}	Maximum Input Capacitance		10	10	10	pF

^{1.} For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{2.} Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Counter)*	35	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Guaranteed Limit			
Symbol	Parameter	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
^t rec	Minimum Recovery Time, Reset Inactive to Clock A or Clock B (Figure 2)	2.0 3.0 4.5 6.0	25 15 10 9	30 20 13 11	40 30 15 13	ns
t _W	Minimum Pulse Width, Clock A, Clock B (Figure 1)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 15	110 36 22 19	ns
t _W	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	75 27 20 18	95 32 24 22	110 36 30 28	ns
t _f , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS Clock A (Pins 1, 15) and Clock B (Pins 4, 15)

Clock A is the clock input to the \div 2 counter; Clock B is the clock input to the \div 5 counter. The internal flip-flops are toggled by high-to-low transitions of the clock input.

CONTROL INPUTS Reset (Pins 2, 14)

Asynchronous reset. A high at the Reset input prevents counting, resets the internal flip-flops, and forces QA through QD low.

OUTPUTS QA (Pins 3, 13)

Output of the \div 2 counter.

QB, QC, QD (Pins 5, 6, 7, 9, 10, 11)

Outputs of the \div 5 counter. QD is the most significant bit. QA is the least significant bit when the counter is connected for BCD output as in Figure 4. QB is the least significant bit when the counter is operating in the bi–quinary mode as in Figure 5.

SWITCHING WAVEFORMS

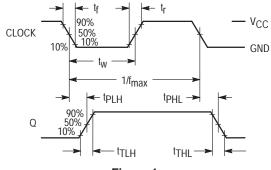


Figure 1.

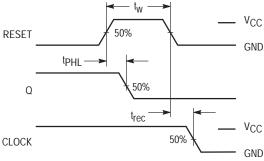
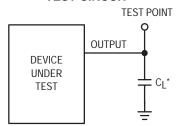


Figure 2.

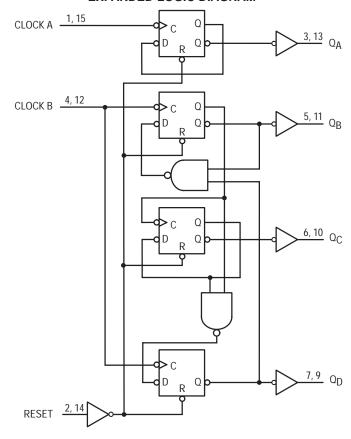
TEST CIRCUIT



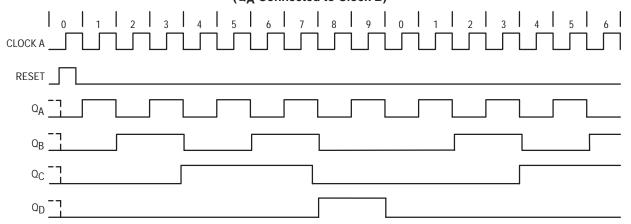
*Includes all probe and jig capacitance

Figure 3.

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM (QA Connected to Clock B)



APPLICATIONS INFORMATION

Each half of the MC54/74HC390A has independent \div 2 and \div 5 sections (except for the Reset function). The \div 2 and \div 5 counters can be connected to give BCD or bi–quinary (2–5) count sequences. If Output QA is connected to the Clock B input (Figure 4), a decade divider with BCD output is obtained. The function table for the BCD count sequence is given in Table 1.

To obtain a bi–quinary count sequence, the input signals connected to the Clock B input, and output QD is connected to the Clock A input (Figure 5). QA provides a 50% duty cycle output. The bi–quinary count sequence function table is given in Table 2.

Table 1. BCD Count Sequence*

	Output					
Count	QD	QС	QB	Q _A		
0	L	L	L	L		
1	L	L	L	Н		
2	L	L	Н	L		
3	L	L	Н	Н		
4	L	Н	L	L		
5	L	Н	L	Н		
6	L	Н	Н	L		
7	L	Н	Н	Н		
8	Н	L	L	L		
9	Н	L	L	Н		

^{*}QA connected to Clock B input.

Table 2. Bi-Quinary Count Sequence**

	Output					
Count	QA	QD	QC	QB		
0	L	L	L	L		
1	L	L	L	Н		
2	L	L	Н	L		
3	L	L	Н	н		
4	L	Н	L	L		
8	Н	L	L	L		
9	Н	L	L	Н		
10	Н	L	Н	L		
11	Н	L	Н	н		
12	Н	Н	L	L		

^{**} QD connected to Clock A input.

CONNECTION DIAGRAMS

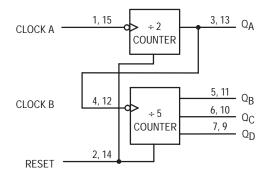


Figure 4. BCD Count

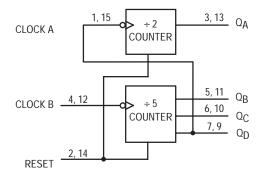
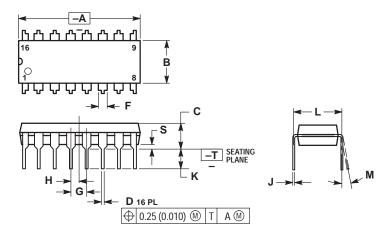


Figure 5. Bi-Quinary Count

PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R

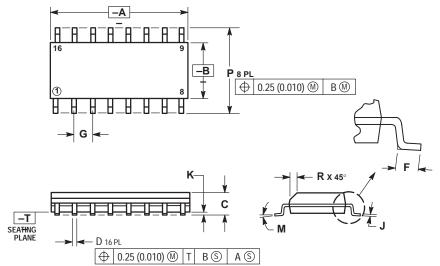


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	LLIMETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.070	1.02	1.77	
G	0.	100 BSC	2	.54 BSC	
Н	0.	050 BSC	1	.27 BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10°	0°	10°	
S	0.020	0.040	0.51	1.01	





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

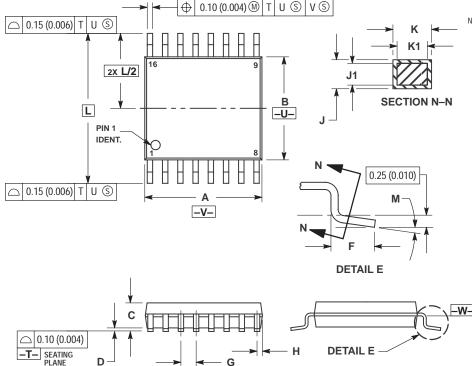
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



16X **K** REF

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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